

Features

- Ultra small package: 1.0x0.6x0.5mm
- Very low capacitance: 2.5pF typical
- Ultra low leakage: nA level
- Low operating voltage: 5V
- Low clamping voltage
- 3-pin leadless package
- Up to 2-line protects
- Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test
Air discharge: $\pm 15\text{kV}$
Contact discharge: $\pm 8\text{kV}$
 - IEC61000-4-4 (EFT) 40A (5/50ns)
- RoHS Compliant

Ordering Information

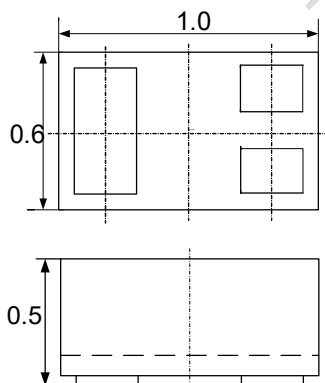
Part Number	Qty per Reel	Reel Size
ESD5V0B2-DFN3	10000	7"

Mechanical Characteristics

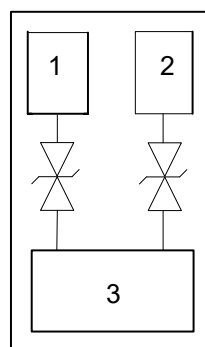
- Package: DFN1006-3 (1.0x0.6x0.5mm)
- Lead Finish: NiPdAu
- Case Material: "Green" Molding Compound.
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminal Connections: See Diagram Below

Applications

- Cellular Handsets & Accessories
- Digital Visual Interface (DVI)
- Display Port
- MDDI Ports
- USB Ports
- PCI Express
- Serial ATA



Package Dimensions



Circuit and Pin Schematic

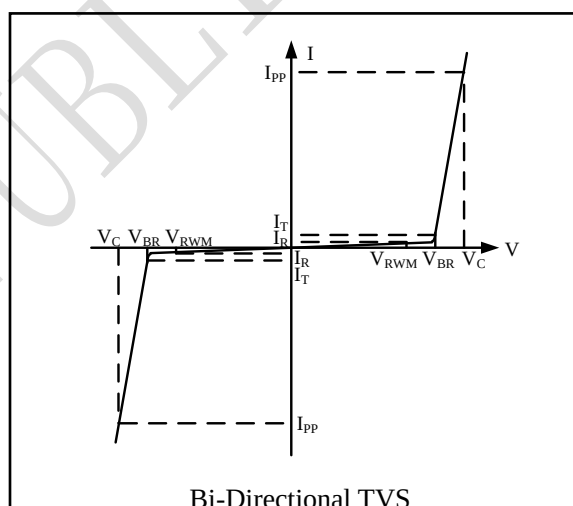
PROTECTION PRODUCTS

Absolute Maximum Rating

Parameter	Symbol	Value	Unit
ESD per IEC 61000-4-2 (Air)	VESD	±15	kV
ESD per IEC 61000-4-2 (Contact)		±8	
Operating Temperature Range	T _J	-55 to +125	°C
Storage Temperature Range	T _{stg}	-55 to +150	°C

ELECTRICAL CHARACTERISTICS PER LINE @ 25°C Unless Otherwise Specified

Symbol	Parameter
V _{RWM}	Nominal Reverse Working Voltage
I _R	Reverse Leakage Current @ V _{RWM}
V _{BR}	Reverse Breakdown Voltage @ I _T
I _T	Test Current for Reverse Breakdown
V _C	Clamping Voltage @ I _{pp}
I _{pp}	Maximum Peak Pulse Current
C _{ESD}	Parasitic Capacitance
V _R	Reverse Voltage
f	Small Signal Frequency



Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	V _{RWM}			5	V	Pin 1 or pin 2 to pin 3 and between pin 1 and pin 2
Breakdown Voltage	V _{BR}	6			V	I _T = 1mA, pin 1 or pin 2 to pin 3 and between pin 1 and pin 2
Reverse Leakage Current	I _R			0.5	μA	V _{RWM} = 5V, pin 1 or pin 2 to pin 3 and between pin 1 and pin 2
Clamping Voltage	V _C			10	V	I _{PP} = 1A (8 x 20μs pulse), pin 1 to pin 3 or pin 2 to pin 3
Junction Capacitance	C _J		2	3	pF	V _R = 0V, f = 1MHz, pin 1 or pin 2 to pin 3

Typical Performance Characteristics ($T_A=25^\circ\text{C}$ unless otherwise Specified)

Fig1. 8/20 μs Pulse Waveform

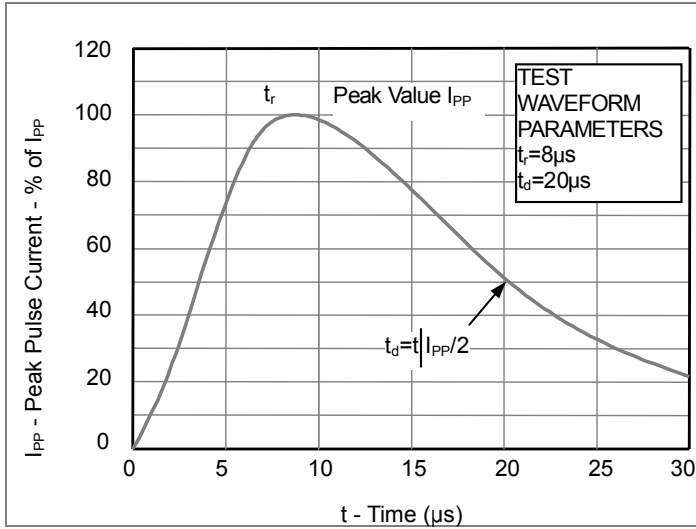


Fig2. ESD Pulse Waveform (according to IEC 61000-4-2)

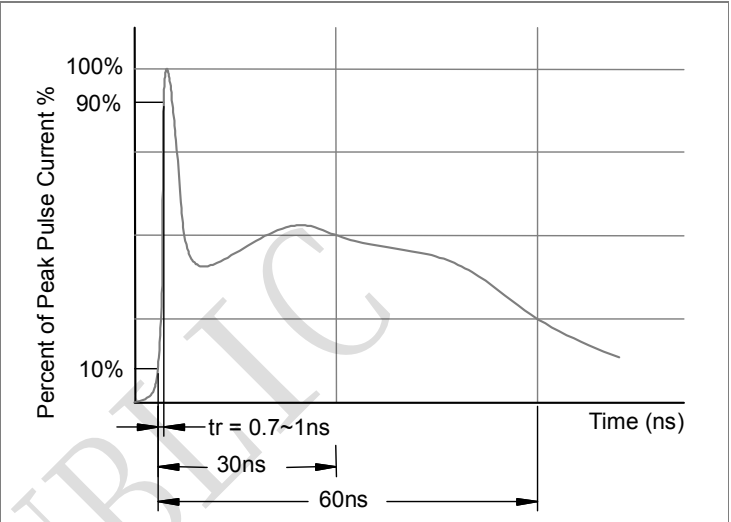
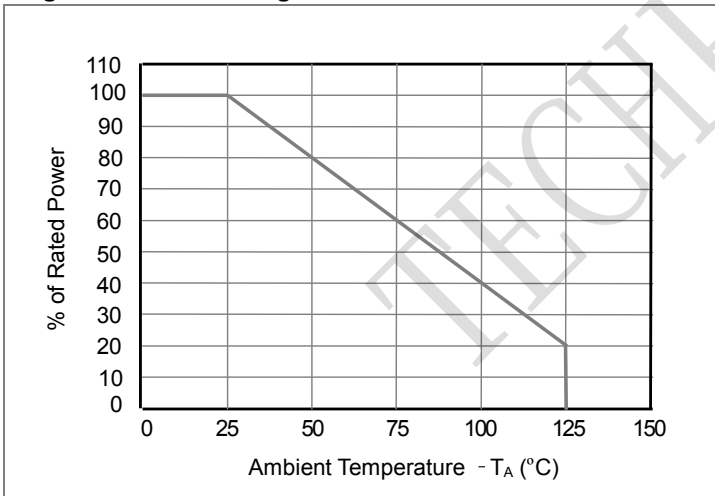
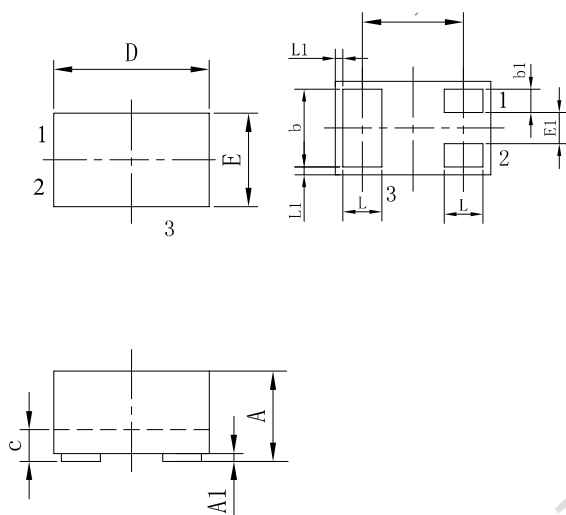


Fig3. Power Derating Curve

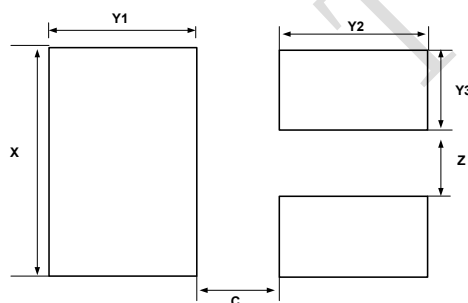


Outline Drawing - DFN1006-3



SYM	DIMENSIONS					
	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.45	0.50	0.55	0.018	0.020	0.022
A1	0.00	0.02	0.05	0.000	0.001	0.002
b	0.45	0.50	0.55	0.018	0.020	0.022
b1	0.10	0.15	0.20	0.004	0.006	0.008
c	0.12	0.15	0.18	0.005	0.006	0.007
D	0.95	1.00	1.05	0.037	0.039	0.041
e	0.65 BSC			0.026 BSC		
E	0.55	0.60	0.65	0.022	0.024	0.026
E1	0.15	0.20	0.25	0.006	0.008	0.010
L	0.20	0.25	0.30	0.008	0.010	0.012
L1	0.05 REF			0.0002 REF		

Land Pattern -DFN1006-3



SYM	DIMENSIONS	
	MILLIMETERS	INCHES
C	0.25	0.010
X	0.65	0.024
Y1	0.50	0.020
Y2	0.50	0.020
Y3	0.25	0.010
Z	0.20	0.008

单击下面可查看定价，库存，交付和生命周期等信息

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